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Attorney Docket No.		NC No. 82,745	
First Inventor or Application Identifier		Chrisey et al	
Title	MATRIX ASSISTED PULSED LASER EVAPORATION DIRECT WRITE		
Express Mail Label No.			

(Only for new nonprovisional applications under 37 C.F.R. § 1.53(b))

ADDRESS TO: Assistant Commissioner for Patents
Box Patent Application
Washington, DC 20231

See MPEP chapter 600 concerning utility patent application contents.

1. ☐ * Fee Transmittal Form (e.g., PTO/SB/17)
(Submit an original and a duplicate for fee processing)
2. ☒ Specification [Total Pages (preferred arrangement set forth below)
- Descriptive title of the Invention
 - Cross References to Related Applications
 - Statement Regarding Fed sponsored R & D
 - Reference to Microfiche Appendix
5. ☐ Microfiche Computer Program (Appendix)
6. Nucleotide and/or Amino Acid Sequence Submission
(if applicable, all necessary)
- a. ☐ Computer Readable Copy
 - b. ☐ Paper Copy (identical to computer copy)
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7. ☒ Assignment Papers (cover sheet & document(s))

8. ☐ 37 C.F.R. §3.73(b) Statement ☐ Power of Attorney
(when there is an assignee)

9. ☒ English Translation Document (if applicable)

10. ☒ Information Disclosure Statement (IDS)/PTO-1449 ☒ Copies of IDS Citations

11. ☒ Preliminary Amendment

12. ☐ Return Receipt Postcard (MPEP 503)
(Should be specifically itemized)

13. ☐ * Small Entity Statement(s) ☐ Statement filed in prior application, Status still proper and desired
(PTO/SB/09-12)

14. ☐ Certified Copy of Priority Document(s)
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15. ☐ Other:


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|---------------------------------------|--|---|---------------------------------------|
| <input type="checkbox"/> Continuation | <input checked="" type="checkbox"/> Divisional | <input type="checkbox"/> Continuation-in-part (CIP) | of prior application No. 09 / 318,134 |
|---------------------------------------|--|---|---------------------------------------|

Prior application information. Examiner M. Padgett
Group / Art Unit: 1762
For CONTINUATION or DIVISIONAL APPS only: The entire disclosure of the prior application, from which an oath or declaration is supplied under Box 4b, is considered a part of the disclosure of the accompanying continuation or divisional application and is hereby incorporated by reference. The incorporation can only be relied upon when a portion has been inadvertently omitted from the submitted application parts.

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Signature			Date 9/27/00

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See 37 C.F.R. §§ 1.27 and 1.28.

TOTAL AMOUNT OF PAYMENT (\$) 720.00

Complete if Known

Application Number
Filing Date May 25, 1999
First Named Inventor Chrisey et al
Examiner Name M. Padgett
Group / Art Unit 1762
Attorney Docket No. NC No. 82,745

METHOD OF PAYMENT (check one)

1. ☒ The Commissioner is hereby authorized to charge indicated fees and credit any overpayments to:

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FEE CALCULATION

1. BASIC FILING FEE

Large Entity Fee Code (\$)	Small Entity Fee Code (\$)	Fee Description	Fee Paid
101 690	201 345	Utility filing fee	690.00
106 310	206 155	Design filing fee	
107 480	207 240	Plant filing fee	
108 690	208 345	Reissue filing fee	
114 150	214 75	Provisional filing fee	

SUBTOTAL (1) (\$) 690.00

2. EXTRA CLAIM FEES

Total Claims	Extra Claims	Fee from below	Fee Paid	
19	-20** = 0	18	0	
Independent Claims	1	-3** = 0	78	0
Multiple Dependent			0	

**or number previously paid, if greater; For Reissues, see below

Large Entity Small Entity

Fee Code (\$)	Fee Code (\$)	Fee Description
103 18	203 9	Claims in excess of 20
102 78	202 39	Independent claims in excess of 3
104 260	204 130	Multiple dependent claim, if not paid
109 78	209 39	** Reissue independent claims over original patent
110 18	210 9	** Reissue claims in excess of 20 and over original patent

SUBTOTAL (2) (\$) 0

FEE CALCULATION (continued)

3. ADDITIONAL FEES

Large Entity Fee Code (\$)	Small Entity Fee Code (\$)	Fee Description	Fee Paid
105 130	205 65	Surcharge - late filing fee or oath	
127 50	227 25	Surcharge - late provisional filing fee or cover sheet	
139 130	139 130	Non-English specification	
147 2,520	147 2,520	For filing a request for reexamination	
112 920*	112 920*	Requesting publication of SIR prior to Examiner action	
113 1,840*	113 1,840*	Requesting publication of SIR after Examiner action	
115 110	215 55	Extension for reply within first month	
116 380	216 190	Extension for reply within second month	
117 870	217 435	Extension for reply within third month	
118 1,360	218 680	Extension for reply within fourth month	
128 1,850	228 925	Extension for reply within fifth month	
119 300	219 150	Notice of Appeal	
120 300	220 150	Filing a brief in support of an appeal	
121 260	221 130	Request for oral hearing	
138 1,510	138 1,510	Petition to institute a public use proceeding	
140 110	240 55	Petition to revive - unavoidable	
141 1,210	241 605	Petition to revive - unintentional	
142 1,210	242 605	Utility issue fee (or reissue)	
143 430	243 215	Design issue fee	
144 580	244 290	Plant issue fee	
122 130	122 130	Petitions to the Commissioner	
123 50	123 50	Petitions related to provisional applications	
126 240	126 240	Submission of Information Disclosure Stmt	
581 40	581 40	Recording each patent assignment per property (times number of properties)	
146 690	246 345	Filing a submission after final rejection (37 CFR § 1.129(a))	
149 690	249 345	For each additional invention to be examined (37 CFR § 1.129(b))	

Other fee (specify) _____

Other fee (specify) _____

* Reduced by Basic Filing Fee Paid

SUBTOTAL (3) (\$)

SUBMITTED BY

Name (Print/Type)	Barry A. Edelberg	Registration No. (Attorney/Agent)	31,012	Telephone	(202)404-1551
Signature		Date	9/27/00		

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PATENT APPLICATION

Docket No.: N.C. 82,745

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Chrisey, et al
Application No.: To be assigned
(Divisional of Appln. No. 09/318,134)
Filed: On even date herewith
For: MATRIX ASSISTED PULSED
LASER EVAPORATION DIRECT
WRITE

Examiner: To be assigned
Group Art Unit: To be assigned

September 26, 2000

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to an examination on the merits, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 1, after the title of the invention, insert the following new paragraph:

--This is a divisional application of copending Application No. 09/318,134, filed May 25, 1999. Application No. 09/318,134 is hereby incorporated herein by reference.--

IN THE CLAIMS:

Please cancel claims 20 through 37.

Application No.: To be assigned
(Divisional of Appln. No. 09/318,134)
Applicant(s): Chrisey, et al

PATENT APPLICATION
Docket No.: N.C. 82,745

REMARKS

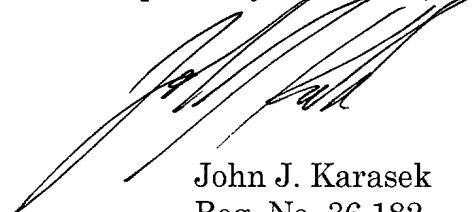
This application has been revised to place it in better condition for examination. Upon entry of this preliminary amendment, only claims 1 through 19 will appear in this case.

A favorable action at the Examiner's earliest convenience is earnestly solicited.

Kindly charge any additional fees due, or credit overpayment of fees, to Deposit Account No. 50-0281.

Prepared by:
Philip Edward Ketner
Reg. No. 46,272
(202)404-1554

Respectfully submitted,



John J. Karasek
Reg. No. 36,182
September 27, 2000



DEPARTMENT OF THE NAVY
NAVAL RESEARCH LABORATORY
4555 OVERLOOK AVE SW
WASHINGTON D C 20375-5320

IN REPLY REFER TO:

Navy Case No. 79,702

APPLICATION FOR LETTERS PATENT

TO ALL WHOM IT MAY CONCERN:

BE IT KNOWN THAT Douglas B. Chrisey, R. Andrew McGill, and Alberto Pique are citizens of the United States of America, and residents of Bowie, MD, Lorton, VA, and Bowie, MD have invented certain new and useful improvements in "MATRIX ASSISTED PULSED LASER EVAPORATION DIRECT WRITE" of which the following is a specification:

Prepared by:
Ralph T. Webb
Reg. No. 33047
Tele. No. (202) 404-1554

MATRIX ASSISTED PULSED LASER EVAPORATION DIRECT WRITE

Background of the Invention**1. Field of the Invention**

The invention relates generally to the deposition of materials and more specifically to devices, materials and methods for direct writing of a wide range of different materials onto substrates.

2. Description of the Related Art

The term "direct write" refers generally to any technique for creating a pattern directly on a substrate, either by adding or removing material from the substrate, without the use of a mask or preexisting form. Direct write technologies have been developed in response to a need in the electronics industry for a means to rapidly prototype passive circuit elements on various substrates, especially in the mesoscopic regime, that is, electronic devices that straddle the size range between conventional microelectronics (sub-micron-range) and traditional surface mount components (10+ mm-range). (Direct writing may also be accomplished in the sub-micron range using electron beams or focused ion beams, but these techniques, because of their small scale, are not appropriate for large scale rapid prototyping.) Direct writing allows for circuits to be prototyped without iterations in photolithographic mask design and allows the rapid evaluation of the performance of circuits too

1 difficult to accurately model. Further, direct writing allows for the size of printed circuit boards and
2 other structures to be reduced by allowing passive circuit elements to be conformably incorporated
3 into the structure. Direct writing can be controlled with CAD/CAM programs, thereby allowing
4 electronic circuits to be fabricated by machinery operated by unskilled personnel or allowing
5 designers to move quickly from a design to a working prototype. Mesoscopic direct write
6 technologies have the potential to enable new capabilities to produce next generation applications
7 in the mesoscopic regime. Other applications of direct write technologies in microelectronic
8 fabrication include forming ohmic contacts, forming interconnects for circuit and photolithographic
9 mask repair, device restructuring and customization, design and fault correction.

10 Currently known direct write technologies for adding materials to a substrate include ink jet
11 printing, Micropen[®], laser chemical vapor deposition (LCVD) and laser engineered nano-shaping
12 (LENS). Currently known direct write technologies for removing material from a substrate include
13 laser machining, laser trimming and laser drilling.

14 The direct writing techniques of ink jet printing, screening and Micropen[®] are wet
15 techniques, that is, the material to be deposited is combined with a solvent or binder and is squirted
16 onto a substrate. The solvent or binder must later be removed by a drying or curing process, which
17 limits the flexibility and capability of these approaches. In addition, wet techniques are inherently
18 limited by viscoelastic properties of the fluid in which the particles are suspended or dissolved.

19 In the direct writing technique known as "laser induced forward transfer" (LIFT), a pulsed
20 laser beam is directed through a laser-transparent target substrate to strike a film of material coated

1 on the opposite side of the target substrate. The laser vaporizes the film material as it absorbs the
2 laser radiation and, due to the transfer of momentum, the material is removed from the target
3 substrate and is redeposited on a receiving substrate that is placed in proximity to the target
4 substrate. Laser induced forward transfer is typically used to transfer opaque thin films, typically
5 metals, from a pre-coated laser transparent support, typically glass, SiO₂, Al₂O₃, SrTiO₃, etc., to the
6 receiving substrate. Various methods of laser-induced forward transfer are described in, for example,
7 the following U.S. patents and publications incorporated herein by reference: U.S. Patent No.
8 4,752,455 to Mayer, U.S. Patent No. 4,895,735 to Cook, U.S. Patent No. 5,725,706 to Thoma et al,
9 U.S. Patent No. 5,292,559 to Joyce, Jr. et al, U.S. Patent No. 5,492,861 to Opower, U.S. Patent No.
10 5,725,914 to Opower, U.S. Patent No. 5,736,464 to Opower, U.S. Patent No. 4,970,196 to Kim et
11 al, U.S. Patent No. 5,173,441 to Yu et al, and Bohandy et al, "Metal Deposition from a Supported
12 Metal Film Using an Excimer Laser, J. Appl. Phys. 60 (4) 15 August 1986, pp 1538 - 1539. Because
13 the film material is vaporized by the action of the laser, laser induced forward transfer is inherently
14 a homogeneous, pyrolytic technique and typically cannot be used to deposit complex crystalline,
15 multi-component materials or materials that have a crystallization temperature well above room
16 temperature because the resulting deposited material will be a weakly adherent amorphous coating.
17 Moreover, because the material to be transferred is vaporized, it becomes more reactive and can
18 more easily become degraded, oxidized or contaminated. The method is not well suited for the
19 transfer of organic materials, since many organic materials are fragile and thermally labile and can
20 be irreversibly damaged during deposition. Moreover, functional groups on an organic polymer can

1 be irreversibly damaged by direct exposure to laser energy. Other disadvantages of the laser induced
2 forward transfer technique include poor uniformity, morphology, adhesion, and resolution. Further,
3 because of the high temperatures involved in the process, there is a danger of ablation or sputtering
4 of the support, which can cause the incorporation of impurities in the material that is deposited on
5 the receiving substrate. Another disadvantage of laser induced forward transfer is that it typically
6 requires that the coating of the material to be transferred be a thin coating, generally less than 1 μm
7 thick. Because of this requirement, it is very time-consuming to transfer more than very small
8 amounts of material.

9 In a simple variation of the laser induced forward deposition technique, the target substrate
10 is coated with several layers of materials. The outermost layer, that is, the layer closest to the
11 receiving substrate, consists of the material to be deposited and the innermost layer consists of a
12 material that absorbs laser energy and becomes vaporized, causing the outermost layer to be
13 propelled against the receiving substrate. Variations of this technique are described in, for example,
14 the following U.S. patents and publications incorporated herein by reference: U.S. Patent No.
15 5,171,650 to Ellis et al, U.S. Patent No. 5,256,506 to Ellis et al, U.S. Patent No. 4,987,006 to
16 Williams et al, U.S. Patent No. 5,156,938 to Foley et al and Tolbert et al, "Laser Ablation Transfer
17 Imaging Using Picosecond Optical pulses: Ultra-High Speed, Lower Threshold and High
18 Resolution" Journal of Imaging Science and Technology, Vol. 37, No. 5, Sept./Oct. 1993pp.485-489.
19 A disadvantage of this method is that, because of the multiple layers, it is difficult or impossible to
20 achieve the high degree of homogeneity of deposited material on the receiving substrate required,

1 for example, for the construction of electronic devices, sensing devices or passivation coatings.

2 Therefore, there is a strong need for devices and methods for transferring materials for uses
3 such as in electronic devices, sensing devices or passivation coatings with in such a way that desired
4 properties of the materials are preserved or enhanced. For example, there is a need for a method to
5 transfer powders or particulate materials so that they retain their bulk properties. With respect to
6 novel materials such as organic polymers that are incorporated into electronic devices, there is a need
7 for a method to transfer these materials in such a way that their structural and chemical integrity is
8 retained.

9 10 **Summary of the Invention**

11 It is an object of the present invention to provide devices, materials and methods for
12 depositing a material on a substrate wherein a pattern can be created directly on the substrate without
13 the use of a mask.

14 It is an object of the present invention to provide a device and method that is useful for
15 depositing a wide range of materials such as complex polymeric materials or complex electronic
16 materials, with no damage to the starting material.

17 It is a further object of the present invention to provide a device and method for depositing
18 a material on a substrate wherein the deposition can be carried out in ambient conditions, that is, at
19 atmospheric pressure and at room temperature.

20 It is a further object of the present invention to provide a device ad method for depositing a

1 material on a substrate by laser induced deposition wherein the spatial resolution of the deposited
2 material can be as small as 1 μm .

3 It is an object of the present invention to provide equipment and a method for creating an
4 electronic device, sensor, or passivation coating by depositing a materials on a substrate in a
5 controlled manner wherein the process can be computer-controlled.

6 It is an object of the present invention to provide equipment and a method for creating an
7 electronic device, sensor or passivation coating by depositing a materials on a substrate in a
8 controlled manner wherein it is possible to switch rapidly between different materials to be deposited
9 on the substrate.

10 These and other objects are achieved by a device and method for depositing a material onto
11 a receiving substrate, the device comprising a source of pulsed laser energy, a receiving substrate,
12 and a target substrate. The target substrate comprises a laser transparent support having a back
13 surface and a front surface. The front surface has a coating that comprises a mixture of the transfer
14 material to be deposited and a matrix material. The matrix material has the property that, when it is
15 exposed to pulsed laser energy, it is more volatile than the transfer material. The source of pulsed
16 laser energy can be positioned in relation to the target substrate so that pulsed laser energy can be
17 directed through the back surface of the target substrate and through the laser-transparent support
18 to strike the coating at a defined location with sufficient energy to volatilize the matrix material at
19 the location, causing the coating to desorb from the location and be lifted from the surface of the
20 support. The receiving substrate can be positioned in a spaced relation to the target substrate so that

1 the transfer material in the desorbed coating can be deposited at a defined location on the receiving
2 substrate and so that the matrix material, or decomposition products thereof, in the desorbed coating
3 can migrate from the space between the receiving substrate and the target substrate.

4 The source of pulsed laser energy and the target substrate can be moved with respect to each
5 other so that after the coating desorbs at one location on the target substrate, the pulsed laser energy
6 can be directed to another location on the target substrate where the coating has not yet desorbed.

7 The source of pulsed laser energy and the receiving substrate can be moved with respect to each
8 other so that the transfer material can be deposited in a pattern. The source of pulsed laser energy
9 can also be directed through a transparent region of the target substrate, or the target substrate can
10 be moved completely out of the way so that the pulsed laser energy strikes the receiving substrate
11 directly and interacts with the receiving substrate or with material already deposited on the receiving
12 substrate. This can be done, for example, to roughen the surface of the receiving substrate or to
13 modify the composition and properties of material that has been deposited.

14 15 **Brief Description of the Drawings**

16 A more complete appreciation of the invention will be readily obtained by reference to the
17 following Description of the preferred Embodiments and the accompanying drawings.

18 Figure 1 is a schematic representation of the apparatus of the present invention.

19 Figures 2a and 2b are schematic representations of the laser transparent substrate, the coating
20 and the receiving substrate before (2a) and after (2b) the depositing of the transfer material on the

1 receiving substrate.

2 Detailed Description of the Preferred Embodiments

3 As schematically illustrated in Figure 1, the apparatus of the present invention includes a
4 pulsed laser 12 that emits pulsed laser energy as depicted by arrow 14. The pulsed laser is positioned
5 so that laser pulses travel through the back surface of the target substrate and through the laser
6 transparent support 15 to strike the coating 16, which comprises a mixture of a transfer material and
7 a matrix material. The receiving substrate 18 is positioned so that when the coating desorbs from the
8 target substrate, the transfer material is deposited on the receiving substrate. The laser, the target
9 substrate and the receiving substrate are connected to laser positioning means 20, target substrate
10 positioning means 22 and receiving substrate positioning means 24, respectively. Figures 2a and 2b
11 schematically illustrate the effects of exposing the coating 16 to the pulsed laser energy 14, whereby
12 the coating 16 desorbs from the surface of the target substrate so that the transfer material 26 is
13 deposited onto the receiving substrate 18.

14 The receiving substrate can be any material, planar or non-planar onto which one may wish
15 to deposit a transfer material. The receiving substrate may be any solid material including, but not
16 limited to, silicon, glass, plastics, metals, and ceramics. The present invention is particularly useful
17 in creating electronic devices such as passive and active components of printed circuit boards (PCBs)
18 or in creating chemoselective coatings for chemical sensors such as surface acoustic wave (SAW)
19 resonators.

20 The transfer material can be any material that one may wish to deposit on a substrate in a

1 defined pattern, including, but not limited to the following:

2 Metals, including, but not limited to silver, nickel, gold, copper, chromium, titanium,
3 aluminum, platinum, palladium, etc., and alloys thereof;

4 Ceramics, including, but not limited to alumina (Al_2O_3), silica and other glasses, and
5 dielectrics (see below);

6 Dielectrics, including, but not limited to alumina, magnesium oxide (MgO), yttrium
7 oxide (Y_2O_3), zirconium oxide (ZrO_2), cerium oxide (CeO_2), etc.;

8 Ferroelectrics, including, but not limited to barium titanate (BaTiO_3), strontium titanate
9 (SrTiO_3), lead titanate (PbTiO_3), lead zirconate (PbZrO_3), potassium niobate (KNbO_3), strontium
10 bismuth tantalate ($\text{SrBi}_2\text{Ta}_2\text{O}_9$), (Ba,SrTiO_3), and solid solution stoichiometric variations thereof,
11 etc. ;

12 Piezoelectrics, including, but not limited to the above mentioned ferroelectrics, quartz, AlN ,
13 etc.;

14 Ferrites, including but not limited to yttrium iron garnet ($\text{Y}_3\text{Fe}_5\text{O}_{12}$), barium zinc ferrite
15 ($\text{Ba}_2\text{Zn}_2\text{Fe}_{12}\text{O}_{19}$), hexagonal ferrites such as barium ferrite, spinel ferrites such as nickel zinc ferrites,
16 manganese zinc ferrite, magnetite (Fe_3O_4), etc.;

17 Electro-optical ceramics, including, but not limited to lithium niobate (LiNbO_3), lithium
18 tantalate (LiTaO_3), cadmium telluride (CdTe), zinc sulfide (ZnS), etc.;

19 Ceramic superconductors, including, but not limited to $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ (YBCO),
20 $\text{Tl}_2\text{CaBa}_2\text{Cu}_3\text{O}_{12}$, $\text{La}_{1.4}\text{Sr}_{0.6}\text{CuO}_{3.1}$, BiSrCACuO , BaKBiO , halide doped fullerenes, etc.;

Inventor's Name: Douglas B. Chrisey, R. Andrew McGill and Alberto Pique

Chalcogenides, including, but not limited to SrS, ZnS, CaS, PbS, etc.;

Chemoselective materials (see below);

Bioselective materials (see below);

Semiconductors, including, but not limited to Si, Ge, GaAs, CdTe, etc.;

Phosphors, including, but not limited to SrS:Eu, SrS:Ce, ZnS:Ag, Y₂O₃:Eu, Zn₂SiO₄:Mn,

etc. and

Transparent conductive oxides, including, but not limited to indium tin oxide, zinc oxide, etc.

For example, if the receiving substrate is a component of an electronic device, the transfer material can be a material having particular desired electronic properties. Examples of electronic materials include metals, dielectrics, ferroelectrics, ferrites, ferrimagnets, ferromagnets, semiconductors, phosphors and electrically conducting organic polymers.

If the receiving substrate is a component of a chemical or biological sensor, the transfer material can be a material that interacts selectively with a particular chemical or biological analyte. Criteria for selecting chemically selective materials for chemical sensing devices are described in detail in McGill et al, "Choosing Polymer Coatings for Chemical Sensors", CHEMTECH, Vol 24, No. 9, pp 27-37 (1994), the disclosure of which is incorporated herein by reference. Examples of chemoselective materials include SXFA (poly(oxy{methyl[4-hydroxy-4,4-bis(trifluoromethyl)but-1-en-1-yl]silylene})), P4V (poly(4-vinylhexafluorocumyl alcohol). Other examples of chemoselective materials include perfluoro-polyethers terminated with a variety of functional groups such as CF₃CH₂OH, polyethylene imines, polysiloxanes, alkylamino pyridyl substituted polysiloxanes,

1 polytetrafluoroethylene, polysilanes, polyesters, polyvinylaldehydes, polyisobutylene,
2 polyvinylesters, polyalkenes, zeolites, aerogels, porous carbon, metals, silicalites, clay materials,
3 cellulose materials, polyanilines, polythiophenes, polypyrroles, fullerenes, cyclodextrins,
4 cyclophanes, calixeranes, crown ethers, and organic dyes.

5 Examples of biochemical materials that can be deposited with the present invention include
6 proteins, oligopeptides, polypeptides, whole cells, biological tissue, enzymes, cofactors, nucleic
7 acids, DNA, RNA, antibodies (intact primary, polyclonal, and monoclonal), antigens,
8 oligosaccharides, polysaccharides, oligonucleotides, lectins, biotin, streptavidin, and lipids.

9 The receiving substrate may be a component of a physical sensing device, such as, for
10 example, a magnetic sensor, optical sensor, temperature sensor, pressure sensor or gas flow sensor.
11 The transfer material may then be an appropriate sensing material, such as a magnetic sensing
12 material, optical sensing material, temperature sensing material, pressure sensing material or gas
13 flow sensing material. Examples of physical sensing transfer materials include magnetic-
14 nonmagnetic multilayers or resonant magnetic oscillators for magnetic sensing, thin film
15 thermocouples for temperature sensing, piezoelectric films or resonators for pressure sensing and
16 simple resistive heater-thermocouple combinations for gas flow sensing.

17 In many instances, the desired properties of a material are due to the presence of functional
18 groups in the material. For example chemoselective polymers such as SXFA and P4V derive their
19 chemoselectivity from functional groups that extend outward from the polymer backbone. A purpose
20 of the present invention is to provide a way to deposit these polymers onto a substrate without

1 damaging or disrupting the functional groups. As another example, some materials have different
2 electronic, mechanical and thermal properties depending on whether they are in bulk form or in the
3 form of single crystals. For instance, a large grain size is desirable for ferroelectrics to achieve a near
4 bulk dielectric constant and large crystalline platelets are desirable for ferrites to minimize
5 demagnetizing forces. The transfer material in the present invention can be in any form ranging from
6 single crystallites to nanophase powders to micron size particulates, depending on the particular
7 intended use for the transferred material and whether bulk-like properties are desired. A purpose of
8 the present invention is to provide a way to deposit such materials so that the desired form of the
9 material is preserved or even improved (such as in depositing material in such a way that it is better
10 connected or bonded than the original material). Typical particle sizes for the transfer material may
11 range from about 10 nm to about 20 μm . For close packing of the transfer material, the transfer
12 material can comprise particles of different size classes, so that smaller particles can fit into
13 interstices between larger particles. For example, for face centered cubic packing of particles, the
14 highest packing density can be achieved by providing particles of three different sizes wherein the
15 ratio of particle sizes is 1 : less than .414 : less than .225.

16 The transfer material may also be coated particles, such as metal or ceramic particles coated
17 with organic materials such as organic precursors.

18 It is the presence of the matrix material that provides the advantages that the present
19 invention has over methods such as laser induced forward transfer (LIFT). The matrix material is
20 selected primarily according to two criteria: the matrix material must be compatible with the transfer

1 material so that the matrix material and the transfer material can be combined into a mixture to form
2 the coating on the front surface of the laser transparent support, and the matrix material must have
3 the property of being more volatile than the transfer material when the coating is exposed to pulsed
4 laser energy so that when the coating is exposed to pulsed laser energy, the matrix material
5 volatilizes or vaporizes, thereby causing the coating to desorb from the surface of the laser
6 transparent support. The amount of matrix material that is used in the coating relative to the amount
7 of the transfer material can be any amount sufficient to accomplish the purposes described above.
8 Typically, the amount will vary according to the particular matrix material and transfer material.

9 Other factors that can be taken into account in selecting the optimum matrix material to go
10 with a particular transfer material include the ability of the matrix material to dissolve or form a
11 colloidal or particulate suspension with the particular transfer material, the melting point, heat
12 capacity, molecular size, chemical composition, spectral absorption characteristics and heat of
13 vaporization of the matrix material (factors that affect the ability of the matrix material to desorb and
14 lift the transfer material from the target substrate) and the reactivity or nonreactivity of the matrix
15 material towards the transfer material.

16 The matrix material may also serve other functions. For example, the presence of the matrix
17 material may aid in the construction of the coating on the target substrate by helping to hold the
18 transfer material in place on the target substrate, especially if the transfer material is a powder. At
19 the same time, the matrix material may help prevent the transfer material from binding too tightly
20 to the surface of the target substrate. The matrix material may also provide a source of particle

1 coating for transfer material that is in the form of a powder and provide a source of additives, binders
2 and dispersants for the transfer material.

3 Another consideration is any special ability a particular matrix material may have to impart
4 protection to a particular transfer material from damage during the lasing, desorption and transfer
5 to the receiving substrate. For example, a matrix material that absorbs laser energy at the same
6 wavelength as an important functional group on the transfer material may serve to protect the
7 transfer material from damage from exposure to the laser energy. Alternatively, a matrix material
8 may be used that absorbs at a wavelength in a spectral region substantially outside that of the transfer
9 material. In this instance, the matrix material transforms pulsed laser energy into kinetic energy, and
10 the kinetic energy is imparted to the transfer material. Examples of matrix materials include but are
11 not limited to addition polymers (see below), condensation polymers (see below), photoresist
12 polymers (see below), water, aryl solvents, especially toluene, acetophenone and nicotinic acid,
13 arene compounds (e.g. naphthalene, anthracene, phenanthrene), t-butylalcohol, halogenated organic
14 solvent, hydrocarbons, ketones, alcohols, ethers, esters, carboxylic acids, phenols and phosphoric
15 acid.

16 The matrix material may also be a polymer that decomposes or "unzips" into volatile
17 components when exposed to laser energy. The volatile decomposition products then act to propel
18 or lift the transfer material into the gas phase. The polymeric matrix material acts as a propellant and
19 at room temperature the propellant products are volatilized away while the transfer material is
20 deposited as a thin film on the receiving substrate.

1 Unzipping mechanisms are typically catalyzed by a photon that is absorbed by the polymer
2 and leads to chain cleavage, formation of a free radical (The free radical can be formed either by a
3 thermally driven process or by a photochemical process) in the chain which then travels down the
4 polymer chain leading to a chain unzipping that can produce the monomer species. The monomer,
5 ejected at high kinetic energies, imparts some of this energy to the transfer material mixed with the
6 polymer. One general controlling factor for depolymerization or unzipping of addition polymers is
7 the ceiling temperature of the polymer. At the ceiling temperature, the rates of polymerization and
8 depolymerization are equal. At temperatures above the ceiling temperature, depolymerization
9 dominates polymerization. Laser radiation allows the high ceiling temperatures required for
10 depolymerization to be reached between radiation pulses.

11 In general, polymeric propellants that are suitable candidates for consideration as matrix
12 materials are taken from the class of polymers called addition polymers. As a subclass of addition
13 polymers, the suitable candidate materials are typically sterically crowded and are generally
14 thermally unstable. The general polymer classes that are of interest with known properties include
15 poly(alkenes), poly(acrylics), poly(methacrylics), poly(vinyls), poly(vinylketones), poly(styrenes),
16 poly(oxides) or polyethers. In general, addition polymers with alpha substituted structures
17 consistently exhibit lower ceiling temperatures than their unsubstituted parent species and are strong
18 candidate materials. Polymers from the class of materials called condensation polymers, as well as
19 the class of materials called photoresist polymers, may also have some utility, especially if they
20 decompose to volatile materials. The spectrum of candidate materials is wide and many polymers

1 propellants can be used as the matrix material. Not all will be ideal in all characteristics. For
2 example, repolymerization of a polymeric matrix material on the receiving substrate may be a
3 problem with some materials. Other factors to be considered in the selection of the matrix material
4 include the absorption of UV laser radiation, volatility of native propellant material, efficiency of
5 the unzipping process, products of unzipping or decomposition and their volatility/toxicity, kinetic
6 energy imparted by the propellant, degree of repolymerization, inertness of binder material, inertness
7 of unzipped or decomposed propellant, cost, availability, purity, and processability with the material
8 of interest to be deposited.

9 Specific polymeric matrix materials include, but are not limited to, the following: polyacrylic
10 acid -butyl ester, nitrocellulose, poly(methacrylic acid)-methyl ester (PMMA), poly(methacrylic
11 acid)-n butyl ester (PBMA), poly(methacrylic acid)-t butyl ester (PtBMA), polytetrafluoroethylene
12 (PTFE), polyperfluoropropylene, poly N-vinyl carbazole, poly(methyl isopropenyl ketone), poly
13 alphamethyl styrene, polyacrylic acid, alpha phenyl-, methyl ester, polyvinylacetate,
14 polyvinylacetate with zincbromide present, poly(oxymethylene), phenol-formaldehyde positive
15 photoresist resins and photobleachable aromatic dyes.

16 The matrix material may also contain components that assist in the bonding of the transfer
17 material to the receiving substrate or that assist in the bonding of particles of the transfer material
18 to each other after they are deposited on the receiving substrate.

19 Examples of possible transfer material - matrix material combinations for the transfer of
20 electronic materials include alumina (transfer material) with phosphoric acid (matrix material),

1 barium titanate (transfer material) with poly(methacrylic acid), n-butyl ester (PBMA) (matrix
2 material), yttrium iron garnet (transfer material) with poly(methacrylic acid), n-butyl ester (PBMA)
3 (matrix material), and nickel (transfer material) with KPR, (a phenol-formaldehyde positive
4 photoresist polymer) (matrix material).

5 Examples of possible transfer material - matrix material combinations for the transfer of
6 chemoselective polymers are SXFA (poly(oxy{methyl[4-hydroxy-4,4-bis(trifluoromethyl)but-1-en-
7 1-yl] silylene})) (transfer material) with *t*-butanol (matrix material) and P4V (poly(4-
8 vinylhexafluorocumyl alcohol)) (transfer material) with acetophenone (matrix material).

9 The transfer material and the matrix material may be combined to form the coating on the
10 front surface of the laser transparent support in any manner that is sufficient to carry out the purpose
11 of the invention. If the transfer material is soluble to some extent in the matrix material, the transfer
12 material may be dissolved in the matrix material. Alternatively, if the transfer material is not soluble
13 in a suitable solvent, the transfer material may be mixed with a matrix material to form a colloidal
14 or particulate suspension or condensed phase. Still another alternative is to combine the matrix
15 material and the transfer material with a solvent that volatilizes after the mixture is applied to the
16 laser transparent support. The matrix material can also include soluble or insoluble dopants, that is,
17 additional compounds or materials that one may wish to deposit onto the film.

18 The mixture of the transfer material and the matrix material may be applied to the front
19 surface of the laser transparent support by any method known in the art for creating uniform coatings
20 on a surface, including, for example, by spin coating, ink jet deposition, jet vapor deposition, spin

1 spray coating, aerosol spray deposition, electrophoretic deposition, pulsed laser deposition, matrix
2 assisted pulsed laser evaporation, thermal evaporation, sol gel deposition, chemical vapor deposition,
3 sedimentation and print screening. Typically, the mixture of the transfer material and the matrix
4 material will be applied to the front surface of the laser transparent substrate to form a coating that
5 is between about .1 μm and about 100 μm in thickness. Preferably, the coating is greater than about
6 1 μm in thickness, and, most preferably, is between about 1 μm and about 20 μm in thickness. The
7 thicker the coating, the more of the transfer material can be transferred at one time, which is an
8 advantage of the present invention over laser transfer methods that use thin films. On the other hand,
9 a coating that is too thick will not desorb when exposed to the pulsed laser.

10 If the mixture of the transfer material and the matrix material is a liquid at room temperature,
11 the mixture may be coated onto the front surface of the laser transparent support and then the mixture
12 may be frozen to form a solid coating. The target substrate may be kept frozen while the coating is
13 being exposed to a source of laser energy during the deposition process.

14 The laser transparent support is typically planar, having a front surface that is coated with
15 the mixture of the transfer material and the matrix material and a back surface that can be positioned
16 so that laser energy can be directed through the support. The composition of the laser transparent
17 support is selected in accordance with the particular type of pulsed laser that is used. For example,
18 if the laser is a UV laser, the laser transparent support may be a UV-transparent material including,
19 but not limited to fused silica or sapphire. If the laser is an IR laser, the laser transparent support may
20 be an IR-transparent material including, but not limited to plastic, silicon, fused silica, or sapphire.

1 Similarly, if the laser is a visible laser, the laser transparent support may be a material that is
2 transparent in the visible range, including, but not limited to soda-lime and borosilicate glasses.

3 Any suitable source of laser energy may be used in the present invention. In general, a pulsed
4 laser is preferred. (As used herein, the terms " pulsed laser" and "source of pulsed laser energy" are
5 used interchangeably to refer to any device that creates a pulsed laser beam.) Lasers for use in
6 accordance with the present invention can be any type such as are generally used with other types
7 of laser deposition. Pulsed lasers are commercially available within the full spectral range from UV
8 to IR. Typically, such lasers emit light having a wavelength in the range of about 157 nm - 1100 nm,
9 an energy density of about 0.05 - 10 J/cm² (typically about 0.1 - 2.0 J/cm²), a pulsewidth of about
10 10⁻¹² - 10⁻⁶ second and a pulse repetition frequency of about 0 to greater than 20,000 Hz. In general,
11 energy density (fluence) affects morphology; higher energies tend to produce deposited films that
12 have larger particles. Examples of suitable lasers include, but are not limited to, pulsed gas lasers
13 such as excimer lasers, i.e. F₂ (157 nm), ArF (193 nm), KrF (248 nm). XeCl (308 nm), XeF (351
14 nm), CO₂, nitrogen, metal vapor, etc., pulsed solid state lasers such as Nd:YAG, Ti:Sapphire, Ruby,
15 diode pumped, semiconductor, etc., and pulsed dye laser systems. Typically, the particular laser is
16 selected with regard to the absorption wavelengths of the matrix material.

17 The source of pulsed laser energy, the target substrate and the receiving substrate can be
18 positioned with respect to each other and moved with respect to each other by any means known in
19 the art for supporting a laser, target substrate and receiving substrate and moving them in a
20 controlled and defined manner. For example, similar positioning means and moving means for a

1 laser, target and receiving substrate are known in the fields of laser transfer deposition and laser
2 induced forward transfer. The laser may be positioned in any location that provides an optical path
3 between itself and the target substrate so that sufficient laser energy can be directed to defined
4 positions on the target substrate. The dimensions of the pulsed laser beam can be controlled by any
5 means known in the art so that only a precisely defined area of the target substrate is exposed to the
6 pulsed laser energy and so that only a precisely defined portion of the coating desorbs. The receiving
7 substrate should be positioned so that when the coating on the target substrate is desorbed, the
8 transfer material can be deposited at a defined location on the receiving substrate. Also, there should
9 be enough space between the target substrate and the receiving substrate so that volatilized matrix
10 material, or byproducts from laser-induced decomposition of the matrix material, can escape from
11 the space between the target substrate and the receiving substrate. Preferably, the receiving substrate
12 is positioned about 10 to about 100 μm from the coating on the front surface of the target substrate.
13 The laser, target substrate, and the receiving substrate should be moveable with respect to each other
14 so that the transfer material can be deposited in a pattern and so that after the coating desorbs at one
15 location on the target substrate, the pulsed laser energy can be directed to another location on the
16 target substrate where the coating has not yet desorbed. For example, to deposit a line of material
17 on the receiving substrate, the laser is moved with respect to the target substrate and the receiving
18 substrate, which may be held stationary with respect to each other. As the laser moves with respect
19 to the substrate, it directs laser energy to a new location on the target substrate where the coating has
20 not yet desorbed, and causes the transfer material to be deposited onto a new location on the

1 receiving substrate. The successive locations may overlap to the extent necessary to create a
2 continuous line of material on the receiving substrate. To increase the thickness of a deposit at a
3 particular location, the laser and the receiving substrate are held stationary with respect to each other
4 and the target substrate is moved with respect to the laser and the receiving substrate so that as the
5 target substrate moves with respect to the laser, laser energy is directed to a new location on the
6 target substrate where the coating has not yet desorbed and since the laser and the receiving substrate
7 are not moved with respect to each other, the transfer material is deposited onto the same location
8 on the receiving substrate in an increasingly thickened deposit. (As used herein, the terms "moving
9 [a] with respect to [b]" or "moving [a] and [b] with respect to each other" mean that either [a] or [b]
10 can be moved to effect a change in their relative position.)

11 The apparatus of the present invention can be adapted so that a plurality of different transfer
12 materials can be deposited consecutively onto a receiving substrate. This may be done by providing
13 a plurality of target substrates each having a different coating with a different transfer material and
14 providing a way to consecutively move each target substrate into a position for depositing material
15 from that target substrate onto the receiving substrate. Consecutive deposition of different transfer
16 materials can also be accomplished by providing a target substrate that is subdivided into a plurality
17 of different subregions that each have a different coating with a different transfer material and
18 providing a way to select a particular subregion and deposit the transfer material from that subregion
19 onto the receiving substrate.

20 The apparatus of the present invention can also be adapted so that an entire pattern of transfer

1 material is deposited simultaneously on a patterned substrate

2 Having described the invention, the following examples are given to illustrate specific
3 applications of the invention, including the best mode now known to perform the invention. These
4 specific examples are not intended to limit the scope of the invention described in this application.
5

6 EXAMPLES

7 **Example 1: Deposition of Alumina (Al_2O_3)**

8 The coating for the target substrate for the deposition of alumina was prepared by mixing 2
9 grams of alumina, in the form of random-shaped powders having an average particle size of $0.3\ \mu\text{m}$,
10 with 1 ml of a matrix material, phosphoric acid, in 9 ml of methanol and then applying the solution
11 to one side of a 5 cm diameter fused silica disc by spin coating to form an $\text{Al}_2\text{O}_3/\text{H}_3\text{PO}_4$ coating
12 about 1 to 2 μm thick. Using an excimer pulsed laser operating at 248 nm and at a fluence of 300
13 mJ/cm^2 , focused through the fused silica disk to strike the coating in a 25 μm laser spot, it was
14 possible to transfer the alumina powders from the silica disc to a receiving substrate surface located
15 25 μm away. Each laser shot produced a 25 μm disc-shaped deposit about 1 μm thick. To create a
16 line of deposited BTO on the substrate, the laser was moved in a line relative to the substrate and the
17 receiving substrate. To increase the thickness of the deposit at a particular location, the laser and the
18 receiving substrate were held stationary to each other for several shots while the target substrate was
19 moved. With this technique, a dielectric layer for a capacitor was formed.
20

Example 2: Deposition of Barium Titanate (BaTiO_3 , also referred to as "BTO")

The coating for the target substrate for the deposition of barium titanate was prepared by mixing 1 gram of BTO, in the form of random-shaped powders having an average particle size of $1\ \mu\text{m}$, with 0.05 grams of a matrix material, poly(methacrylic acid), n-butyl ester (PBMA) in 10 ml of chloroform and then applying the solution to one side of a 5 cm diameter fused silica disc by spin coating to form a BTO/PBMA coating about 1 to $2\ \mu\text{m}$ thick. Using an excimer pulsed laser operating at 248 nm and at a fluence of $400\ \text{mJ}/\text{cm}^2$, focused through the fused silica disk to strike the coating in a $25\ \mu\text{m}$ laser spot, it was possible to transfer the BTO powders from the silica disc to a receiving substrate surface located $25\ \mu\text{m}$ away. Each laser shot produced a $25\ \mu\text{m}$ disc-shaped deposit about $1\ \mu\text{m}$ thick. To create a line of deposited BTO on the substrate, the laser was moved in a line relative to the substrate and the receiving substrate. To increase the thickness of the deposit at a particular location, the laser and the receiving substrate were held stationary to each other for several shots while the target substrate was moved. With this technique, a dielectric layer for a capacitor was formed.

Example 3: Deposition of Yttrium Iron Garnet ($\text{Y}_3\text{Fe}_5\text{O}_{12}$, also referred to as "YIG")

The coating for the target substrate for the deposition of yttrium iron garnet was prepared by mixing 1 gram of YIG, in the form of spherical powders having an average particle size of $1\ \mu\text{m}$, with 0.05 grams of a matrix material, poly(methacrylic acid), n-butyl ester (PBMA) in 10 ml of chloroform and then applying the solution to one side of a 5 cm diameter fused silica disc by spin coating to form a YIG/PBMA coating about 1 to $2\ \mu\text{m}$ thick. Using an excimer pulsed laser

1 operating at 248 nm and at a fluence of 400 mJ/cm², focused through the fused silica disk to strike
2 the coating in a 25 μ m laser spot, it was possible to transfer the YIG powders from the silica disc
3 to a receiving substrate surface located 25 μ m away. Each laser shot produced a 25 μ m disc-shaped
4 deposit about 1 μ m thick. To create a line of deposited BTO on the substrate, the laser was moved
5 in a line relative to the substrate and the receiving substrate. To increase the thickness of the deposit
6 at a particular location, the laser and the receiving substrate were held stationary to each other for
7 several shots while the target substrate was moved. With this technique, a ferrite core for an inductor
8 was formed.

9 **Example 4: Deposition of Nickel**

10 The coating for the target substrate for the deposition of nickel was prepared by mixing 2
11 grams of nickel, in the form of spherical powders having an average particle size of 1 μ m, with 10
12 ml of a matrix material, diazonaphthoquinone-novolac (a phenol-formaldehyde positive photoresist
13 polymer sold by Kodak under the tradename "KPR") and then applying the solution to one side of
14 a 5 cm diameter fused silica disc by spin coating to form a nickel/KPR coating about 1 to 2 μ m
15 thick. Using an excimer pulsed laser operating at 248 nm and at a fluence of 450 mJ/cm², focused
16 through the fused silica disk to strike the coating in a 40 μ m laser spot, it was possible to transfer
17 the YIG powders from the silica disc to a receiving substrate surface located 25 μ m away. Each laser
18 shot produced a 40 μ m disc-shaped deposit about 0.3 μ m thick. To create a line of deposited nickel
19 on the substrate, the laser was moved in a line relative to the substrate and the receiving substrate.
20 To increase the thickness of the deposit at a particular location, the laser and the receiving substrate

1 were held stationary to each other for several shots while the target substrate was moved. With this
2 technique, various lines of deposited nickel were formed.

3 Obviously, many modifications and variations of the present invention are possible in light
4 of the above teachings. It is therefore to be understood that, within the scope of the appended claims,
5 the invention may be practiced otherwise than as specifically described.

Claims

What is claimed is:

1. An apparatus for depositing a transfer material onto a receiving substrate, the apparatus comprising

a source of pulsed laser energy,

a receiving substrate, and

a target substrate comprising a laser-transparent support having a back surface and a front surface, wherein the front surface has a coating that comprises a mixture of the transfer material to be deposited and a matrix material, wherein the matrix material has the property of being or becoming more volatile than the transfer material when exposed to pulsed laser energy,

means for positioning the source of pulsed laser energy in relation to the target substrate so that pulsed laser energy can be directed through the back surface of the target substrate and through the laser-transparent support to strike the coating at a defined location with sufficient energy to cause the coating to desorb from the location and be lifted from the surface of the support,

means for positioning the receiving substrate in a spaced relation to the target substrate so that the matrix material, or decomposition products thereof, in the desorbed coating can migrate

from the space between the receiving substrate and the target substrate, and so that the transfer material in the desorbed coating can be deposited at a defined location on the receiving substrate.

2. The apparatus of claim 1 wherein the transfer material is in the form of particles and wherein the coating is a colloidal or particulate suspension of the transfer material in the matrix material.
3. The apparatus of Claim 1 wherein the transfer material is in the form of particles having a grain size of between about 10 nm and about 20 μm .
4. The apparatus of Claim 1 wherein the transfer material is a mixture of particles having different grain sizes.
5. The apparatus of Claim 1 wherein the transfer material is an electronic material selected from the group consisting of metals, dielectrics, ferroelectrics, ferrites, ferrimagnets, ferromagnets, phosphors, and semiconductors.
6. The apparatus of Claim 1 wherein the transfer material is a polymer.
7. The apparatus of Claim 1 wherein the transfer material comprises metal or ceramic particles coated with organic precursors.

8. The apparatus of Claim 1 wherein the receiving substrate is a component of a sensing device and the transfer material is a sensing material selected from the group consisting of chemically selective material, biologically selective material, magnetic sensing material, optical sensing material, pressure sensing material, temperature sensing material, porosity selective material and gas flow sensing material.

9. The apparatus of Claim 1 wherein the matrix material is a material that decomposes into volatile components when exposed to pulsed laser energy.

10. The apparatus of Claim 9 wherein the matrix material is an addition polymer.

11. The apparatus of Claim 9 wherein the matrix material is selected from the group consisting of poly(alkenes), poly(acrylics), poly(methacrylics), poly(vinyls), poly(vinylketones), poly(styrenes), poly(oxides) and polyethers.

12. The apparatus of Claim 9 wherein the matrix material is selected from the group consisting of polyacrylic acid -butyl ester, nitrocellulose, poly(methacrylic acid)-methyl ester (PMMA), poly(methacrylic acid)-n butyl ester (PBMA), poly(methacrylic acid)-t butyl ester (PtBMA), polytetrafluoroethylene (PTFE), polyperfluoropropylene, poly N-vinyl carbazole, poly(methyl

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isopropenyl ketone), poly alphamethyl styrene, polyacrylic acid, alpha phenyl-, methyl ester, polyvinylacetate, polyvinylacetate/zincbromide , poly(oxymethylene), phenol-formaldehyde positive photoresist resins and photobleachable aromatic dyes.

13. The apparatus of Claim 1 wherein the matrix material is selected from the group consisting of water, aryl solvents, arene solvents, halogenated organic solvents, hydrocarbons, ketones, esters, ethers, carboxylic acids, phenols and phosphoric acid.

14. The apparatus of Claim 1 further including means for moving the source of pulsed laser energy and the target substrate with respect to each other so that after the coating desorbs at one location on the target substrate, the pulsed laser energy can be directed to another location on the target substrate where the coating has not yet desorbed, and

means for moving the source of pulsed laser energy and the receiving substrate with respect to each other so that the transfer material can be deposited in a pattern.

15. The apparatus of Claim 1 wherein the apparatus further includes a mask interposed between the source of laser energy and the target substrate.

16. The apparatus of Claim 1 wherein the coating on the front surface of the target substrate has been formed by a process of combining the transfer material and the matrix material to form a

mixture and applying the mixture to the front surface of the target substrate by a coating method selected from the group consisting of spin coating, ink jet deposition, jet vapor deposition, spin spray coating, aerosol spray deposition, electrophoretic deposition, pulsed laser deposition, matrix assisted pulsed laser evaporation, thermal evaporation, sol gel deposition, chemical vapor deposition, sedimentation and screen printing.

17. The apparatus of Claim 1 wherein the coating on the front surface of the target substrate has a thickness of between about .1 μm and about 100 μm .

18. The apparatus of Claim 1 wherein the coating on the front surface of the target substrate has a thickness of between about 1 μm and about 20 μm .

19. The apparatus of Claim 1, further including means to position the source of pulsed laser energy with respect to the receiving substrate so that the pulsed laser energy can be directed to strike the receiving substrate whereby the receiving substrate can be pretreated or whereby a transfer material deposited on the substrate can be annealed or etched.

20. A method for depositing a transfer material onto a receiving substrate, the method comprising the steps of

providing a source of pulsed laser energy,

providing a receiving substrate

providing a target substrate comprising a laser-transparent support having a back surface and a front surface, wherein the front surface has a coating that comprises a mixture of the transfer material and a matrix material, wherein the matrix material has the property of being or becoming more volatile than the transfer material when exposed to pulsed laser energy,

positioning the source of pulsed laser energy in relation to the target substrate and exposing the target substrate to pulsed laser energy so that the pulsed laser energy is directed through the back surface of the target substrate and through the laser-transparent support to strike the coating at a defined location with sufficient energy to volatilize the matrix material at the location, causing the coating to desorb from the location and be lifted from the surface of the support,

positioning the receiving substrate in a spaced relation to the target substrate so that the transfer material in the desorbed coating is deposited at defined location on the receiving substrate and so that the matrix material, or decomposition products thereof, in the desorbed coating can migrate from the space between the receiving substrate and the target substrate.

21. The method of Claim 20 wherein the transfer material is in the form of particles and wherein the coating is a colloidal or particulate suspension of the transfer material in the matrix material.

22. The method of Claim 20 wherein the steps of the method are carried out under ambient

conditions.

23. The method of Claim 20 wherein the transfer material is in the form of particles having a grain size of between about 10 nm and about 20 μm .

24. The method of Claim 20 wherein the transfer material is a mixture of particles having different grain sizes.

25. The method of Claim 20 wherein the transfer material comprises metal or ceramic particles coated with organic precursors.

26. The method of Claim 20 wherein the matrix material is a material that decomposes into volatile components when exposed to pulsed laser energy.

27. The method of Claim 26 wherein the matrix material is an addition polymer.

28. The method of Claim 26 wherein the matrix material is selected from the group consisting of poly(alkenes), poly(acrylics), poly(methacrylics), poly(vinyls), poly(vinylketones), poly(styrenes), poly(oxides) and polyethers.

29. The method of Claim 26 wherein the matrix material is selected from the group consisting of polyacrylic acid –butyl ester, nitrocellulose, poly(methacrylic acid)-methyl ester (PMMA), poly(methacrylic acid)-n butyl ester (PBMA), poly(methacrylic acid)-t butyl ester (PtBMA), polytetrafluoroethylene (PTFE), polyperfluoropropylene, poly N-vinyl carbazole, poly(methyl isopropenyl ketone), poly alphamethyl styrene, polyacrylic acid, alpha phenyl-, methyl ester, polyvinylacetate, polyvinylacetate/zincbromide , poly(oxymethylene), phenol-formaldehyde positive photoresist resins and photobleachable aromatic dyes.

30. The method of Claim 20 wherein the coating on the front surface of the target substrate has been formed by a process of combining the transfer material and the matrix material to form a mixture and applying the mixture to the front surface of the target substrate by a coating method selected from the group consisting of spin coating, ink jet deposition, jet vapor deposition, spin spray coating, aerosol spray deposition, electrophoretic deposition, pulsed laser deposition, matrix assisted pulsed laser evaporation, thermal evaporation, sol gel deposition, chemical vapor deposition, sedimentation and screen printing.

31. The method of Claim 20 wherein the coating on the front surface of the target substrate has a thickness of between about .1 μm and about 100 μm .

32. The method of Claim 20 wherein the coating on the front surface of the target substrate has a

thickness of between about 1 μm and about 20 μm .

33. The method of Claim 20 wherein the matrix material is selected from the group consisting of water, aryl solvents, arene solvents, halogenated organic solvents, hydrocarbons, ketones, esters, ethers, carboxylic acids, phenols and phosphoric acid.

34. The method of Claim 20, further including the steps of moving the source of pulsed laser energy and the target substrate with respect to each other so that after the coating desorbs at one location on the target substrate, the source of pulsed laser energy is directed to another location on the target substrate where the coating has not yet desorbed, and

moving the source of pulsed laser energy and the receiving substrate with respect to each other so that the transfer material is deposited in a pattern.

35. The method of claim 20 wherein the receiving substrate is a component of an electronic device and the transfer material is an electronic material selected from the group consisting of metals, dielectrics, ferroelectrics, ferrites, ferrimagnets, ferromagnets, phosphors and semiconductors.

36. The method of claim 20 wherein the receiving substrate is a component of a sensing device and the transfer material is a sensing material selected from the group consisting of chemically

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selective material, biologically selective material, magnetic sensing material, optical sensing material, pressure sensing material, temperature sensing material, and gas flow sensing material.

37. The method of claim 20 including the further step of positioning the source of pulsed laser energy with respect to the receiving substrate so that the pulsed laser energy can be directed to strike the receiving substrate whereby the receiving substrate can be pretreated or whereby a transfer material deposited on the substrate can be annealed or etched.

ABSTRACT

An device for depositing a transfer material onto a receiving substrate includes a source of pulsed laser energy, a receiving substrate, and a target substrate. The target substrate comprises a laser transparent support having a back surface and a front surface. The front surface has a coating that comprises a mixture of the transfer material to be deposited and a matrix material. The matrix material is a material that has the property that, when it is exposed to pulsed laser energy, it is more volatile than the transfer material. The source of pulsed laser energy is be positioned in relation to the target substrate so that pulsed laser energy is directed through the back surface of the target substrate and through the laser-transparent support to strike the coating at a defined location with sufficient energy to volatilize the matrix material at the location, causing the coating to desorb from the location and be lifted from the surface of the support. The receiving substrate is positioned in a spaced relation to the target substrate so that the transfer material in the desorbed coating can be deposited at a defined location on the receiving substrate.

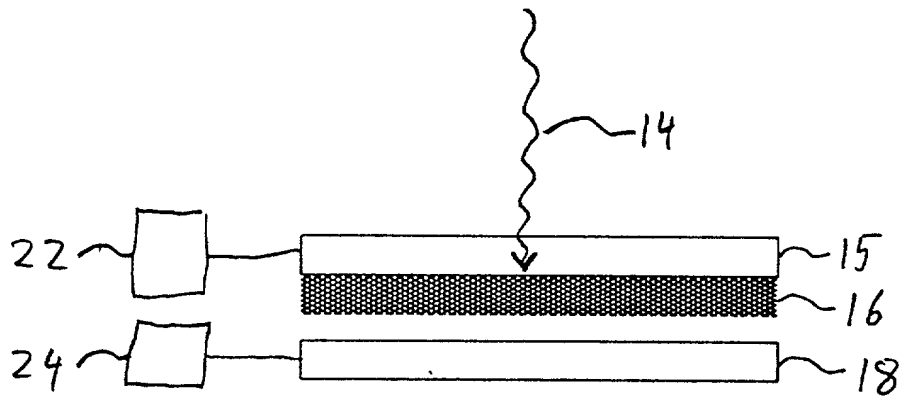
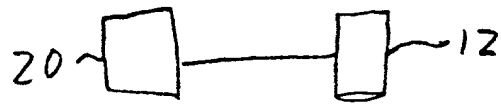


Fig. 1

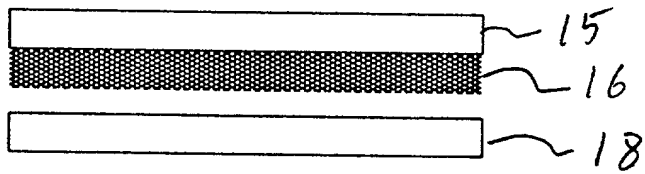


Fig. 2a

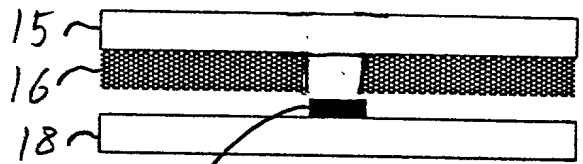


Fig. 2b

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DECLARATION
AND POWER OF ATTORNEY

Navy Case No. 79,702

Page 1 of 2

As a below named inventor, I hereby declare that: My residence, post office address and citizenship are as stated below next to my name. I believe I am the original, first, and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: MATRIX-ASSISTED PULSED LASER EVAPORATION DIRECT WRITE, the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, §1.56(a).

I hereby claim foreign priority benefits under Title 35, United States Code, §119 of any foreign applications for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Number	Country	Filing Date	Priority (Yes/No)

I hereby claim the benefit under Title 35, United States Code, §120 of any United States applications listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of title 35, United States Code, §112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, §1.56(a) which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

U.S. Appl. Serial No.	U.S. Filing Date	Status (patented/pending/abandoned)
60/117,468	January 27, 1999	provisional

POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorneys/and/or agent/s/ to prosecute this application and transact all business in the Patent and Trademark Office connected therewith, and hereby certify that the Government of the United States has the irrevocable right to prosecute this application:

Thomas E. McDonnell, Reg. No. 26,950 and Ralph T. Webb, Reg. No. 33,047.

SEND CORRESPONDENCE TO:

Associate Counsel (Patents), Code 3008.2
Naval Research Laboratory
Washington, D.C. 20375-5000

DIRECT TELEPHONE CALLS TO:

Ralph T. Webb
Reg. No. 33,047
(202) 404-1554

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full name of joint inventor 1: Douglas B. Chrisey

Inventor's signature: Douglas B. Chrisey

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Navy Case No. 79,702
Page 2 of 2

Inventor's signature:

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[illegible]

DECLARATION
AND POWER OF ATTORNEY

Navy Case No. 79,702
Page 1 of 2

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I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

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Full name of joint inventor 1: Douglas B. Chrisey

Inventor's signature: _____

DATE: _____

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